

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
22 September 2005 (22.09.2005)

PCT

(10) International Publication Number  
**WO 2005/088739 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 33/00**

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(21) International Application Number:

PCT/JP2005/004894

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(22) International Filing Date: 14 March 2005 (14.03.2005)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

2004-073059 15 March 2004 (15.03.2004) JP  
60/555,417 23 March 2004 (23.03.2004) US

(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

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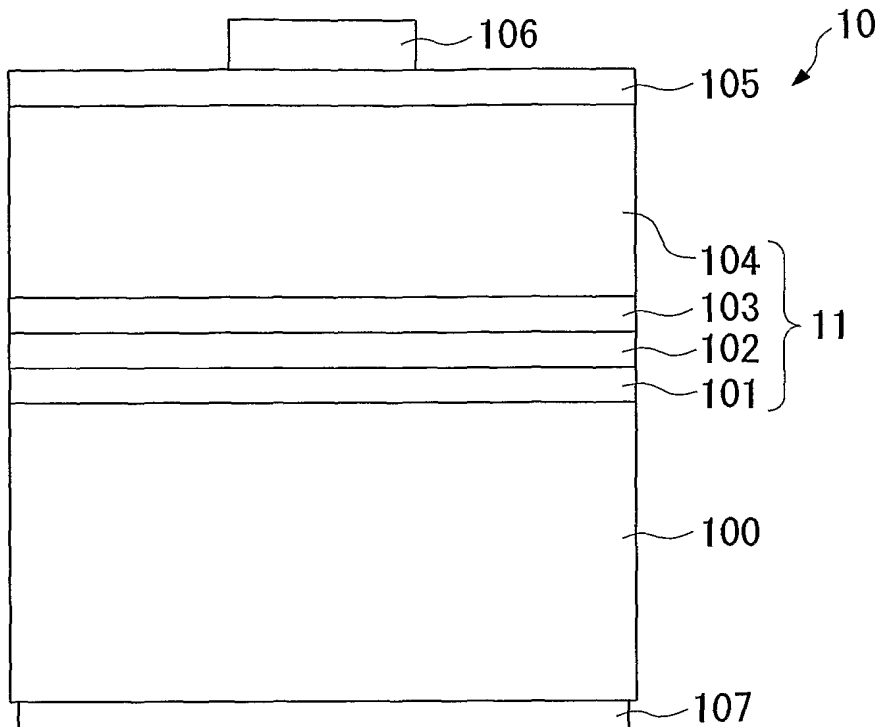
(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,

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[Continued on next page]

(54) Title: COMPOUND SEMICONDUCTOR LIGHT-EMITTING DIODE



(57) Abstract: A compound semiconductor light-emitting diode comprising a light-emitting layer composed of a Group III-V compound semiconductor, and a current diffusion layer provided on the light-emitting layer and composed of a Group III-V compound semiconductor, characterized in that the current diffusion layer is composed of a conductive boron-phosphide-based semiconductor and has a bandgap at room temperature wider than that of the light-emitting layer.

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SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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**Published:**

— *with international search report*